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OFFICIAL FAX**PROPOSED AMENDMENT**

U.S. Serial No.: 09/614,407
Confirmation No.: 1903
Filing Date: July 12, 2000
Inventors: Zheng, et al.
Examiner: E. Smith-Hicks
Group Art Unit: 1741

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*Spec supp
cited as
shown.*

PROPOSED AMENDMENTS
FOR 09/614,407

Please amend the claims as follows:

85. (Amended) A method of depositing a metal on a substrate having one or more features formed thereon, comprising:

applying a first biasing voltage to the substrate while immersing the substrate into an electrolyte solution contained in an electrolyte container comprising an anode immersed in the electrolyte solution, wherein the first biasing voltage [increases over time] is negative relative to the anode; and — p15, l23-24

applying a plating voltage to the substrate once the substrate has been immersed into the electrolyte solution, the plating voltage being higher than the initial portion of the first biasing voltage.

86. (Amended) The method of claim 85, wherein the first biasing voltage [is] provides a ramping [voltage] current. pg 12, l28-30 p16, l9, 10

87. (Amended) The method of claim 85, wherein the first biasing voltage [increases from about zero volt to a range of about 1 volt to about 5 volts] is about 0.8 volt. pg 12, line 1, 28

88. The method of claim 85, wherein the first biasing voltage is configured to limit etching by the electrolyte solution of a seed layer disposed on the one or more features formed on the substrate.

89. (Amended) The method of claim [85] 94, wherein the first biasing voltage and the second biasing voltage [is] are applied for about [0.125] 0.25 second to about [1 second] 5 seconds. pg 16, l11-12

90. (Amended) The method of claim 85, wherein the first biasing voltage [increases from about zero volt to a range of] ranges from about 1 volt to about 5 volts [in a period of about 0.125 second to about 1 second]. pg 15, line 24